SILICON TRANSISTOR

AUDIO FREQUENCY AMPLIFIER, SWITCHING NOPN SILICON EPITAXIAL TRANSISTORS

FEATURES

NEC

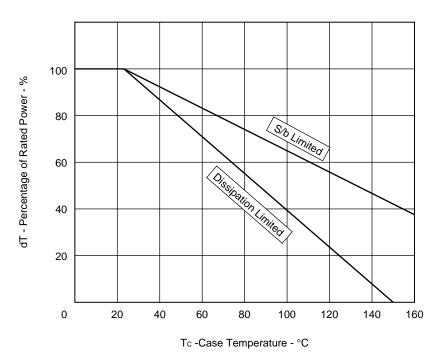
 Low V_{CE(sat)} V_{CE(sat)} = 0.15 V Max (@lc/lB = 1.0 A/5 High DC Current Gain hEF = 150 to 600 (@V_{CE} = 2.0 V, lc = 	·	
ABSOLUTE MAXIMUM RATINGS		
Maximum Voltage and Current (TA = 25	5 °C)	
Collector to Base Voltage	Vcb0	30 V
Collector to Emitter Volteage	VCE0	30 V
Emitter to Base Voltage	Veb0	6.0 V
Collector Current (DC)	IC(DC)	5.0 A
Collector Current (Pulse)*	C(Pulse)	10 A
Base Current (DC)	B(DC)	2.0A
* PW \leq 10ms, Duty Cycle \leq 10 %		
Maximum Power Dissipation		
Total Power Dissipation (Tc = 25 °C)	Рт	10 W
Total Power Dissipation (T _A = 25 °C)	Рт	1.0 W
Maximum Temperature		
Junction Temperature	Tj	150 °C
Storage Temperature	Tstg -	-55 to 150 °C

PACKAGE DIMENSIONS in millimeters (inches) 8.5 MAX. 2.8 MAX. (0.334 MAX.) (0.110 MAX.) 3.8 ± 0.2 (0.149) $\phi 3.2 \pm 0.2 \ (\phi 0.126)$ 126 12.0 MAX (0.472 MAX 00 3 2 1 2.5 ± 0.2 (0.098). 13.0 MIN. (0.512 MIN.) 1.2 (0.047)0.55+0.08 (0.021)0.8+0.08 (0.031)1.2 2.3 2.3 (0.047)(0.090) (0.090) 1. Emitter 2. Collector connected to mounting plane 3. Base

ELECTRICAL CHARACTERISTICS (TA = 25 °C)

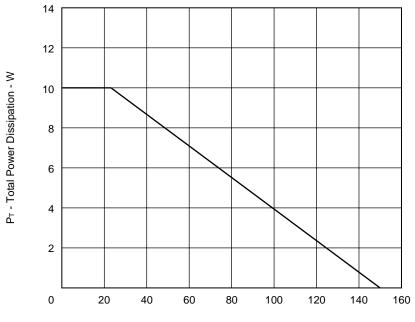
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Collector Cutoff Currnet	Ісво	$V_{CB} = 30 \text{ V}, \text{ Ie} = 0$			100	nA
Emitter Cutoff Current	Іево	$V_{EB} = 6.0 \text{ V}, \text{ Ic} = 0$			100	nA
DC Current Gain	hfe1	Vce = 2.0 V, Ic = 1.0 A	150		600	_
DC Current Gain	hFE2	Vce = 2.0 V, Ic = 4.0 A	50			_
Collector Saturation Voltage	VCE(sat)1	Ic = 1.0 A, I _B = 50 mA		0.07	0.15	V
Collector Saturation Voltage	VCE(sat)2	Ic = 2.0 A, I _B = 0.1 A		0.13	0.25	V
Collector Saturation Voltage	VCE(sat)3	Ic = 4.0 A, I _B = 0.2 A		0.24	0.50	V
Base Saturation Voltage	VBE(sat)	Ic = 2.0 A, I _B = 0.1 A		0.86	1.50	V
Gain Bandwidth Product	f⊤	Vce = 10 V, Ie = 50 mA		120		MHz
Output Capacitance	Cob	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		77		pF

The information in this document is subject to change without notice.

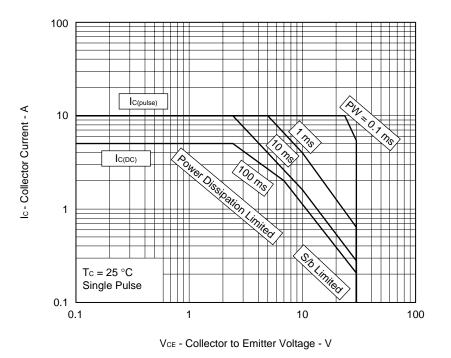


DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA

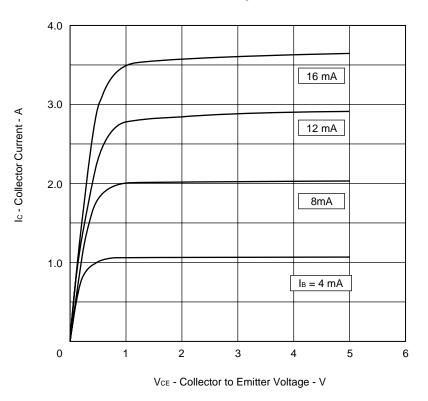




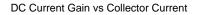
Tc -Case Temperature - °C

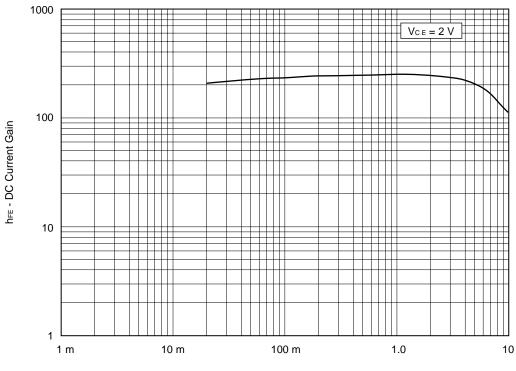


FORWARD BIAS SAFE OPERATING AREA

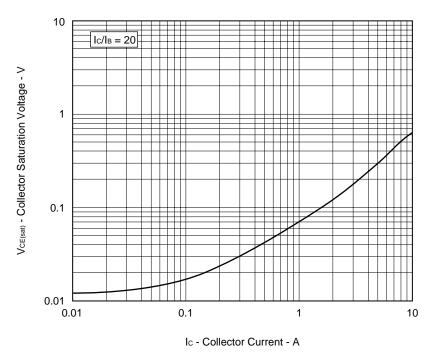


Collector to Emitter Voltage vs Collector Current



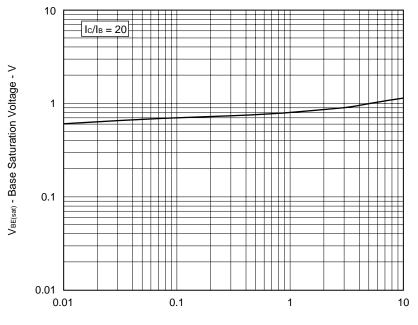


Ic - Collector Current - A

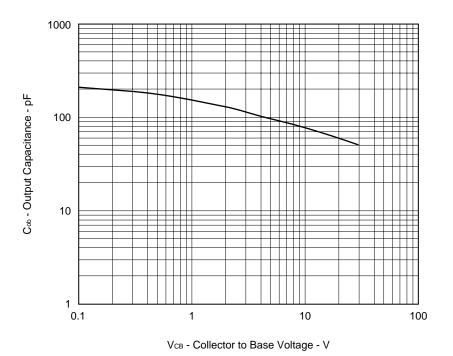


COLLECTOR SATURATION VOLTAGE vs COLLECTOR CURRENT





Ic - Collector Current - A



OUTPUT CAPACITANCE vs COLLECTOR TO BASE VOLTAGE

REFERENCE

Document Name	Document No.		
NEC semiconductor device reliability/quality control system	TEI-1202		
Quality grade on NEC semiconductor devices	IEI-1209		
Semiconductor device mounting technology manual	C10535E		
Semiconductor device package manual	C10943X		
Guide to quality assurance for semiconductor devices	MEI-1202		
Semiconductor selection guide	X10679E		

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Anti-radioactive design is not implemented in this product.